SILICON PHOTODIODE CHIPS
DEVICE NO. : PD-0324

1. Scope :

This specification applies to PN silicon photodiode chips,
Device no. PD-0324.

2. Structure :

2-1. Planar type : PN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy.

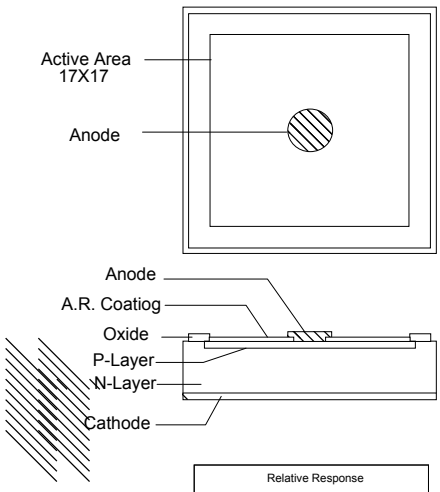
3. Size :

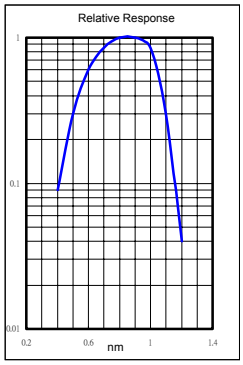
3-1. Chip size : 24 mils × 24 mils (0.610 mm × 0.610 mm).
3-2. Chip thickness : 7.5 ± 1.5 mils (0.19± 0.038 mm).
3-3. Active area : 17 mils × 17 mils (0.432 mm × 0.432 mm).
3-4. Bonding pad (Anode) : 5.0 mils (0.127 mm) diameter.
3-5. Pattern drawing : refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark Current	I_D	V_R=10V H=0mw/cm^2			10	nA
Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA H=0mw/cm^2	33			V
Open circuit Voltage	Voc	C_T=2870° K H=5mw/cm^2		420		mV
Short circuit Current	sc	C_T=2870° K H=5mw/cm^2		1.5		μA
Reverse light current	I_L	V_R =5V C_T=2870° K H=5mw/ cm^2	1.8	2.0	2.2	μA
Total Capacitance	Ct	V_R =5V H=0mw/cm^2 f=1MHz		5		pF
Series Resistance	Rs	V_R =5V H=0mw/cm^2 f=1MHz		200		Ω
Forward Voltage	V_F	I_F=20mA H=0mw/cm^2			1.3	V

PATTERN DRAWING
UNIT:mil





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OPTO TECH CORPORATION
Tel: 886-3-5777481
Fax: 886-3-5795718
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